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ABSTRACT OF THE DISCLOSURE

[0040] A method for fabricating a polysilicon emitter bipolar transistor employs a pair of ion implant methods. A first of the ion implant methods implants a portion of an intrinsic base region interposed between an extrinsic base region and a polysilicon emitter layer with an amorphizing non-active dopant. A second of the ion implant methods implants the polysilicon emitter layer with an active dopant to form a doped polysilicon emitter layer. The polysilicon emitter bipolar transistor is fabricated with enhanced performance.